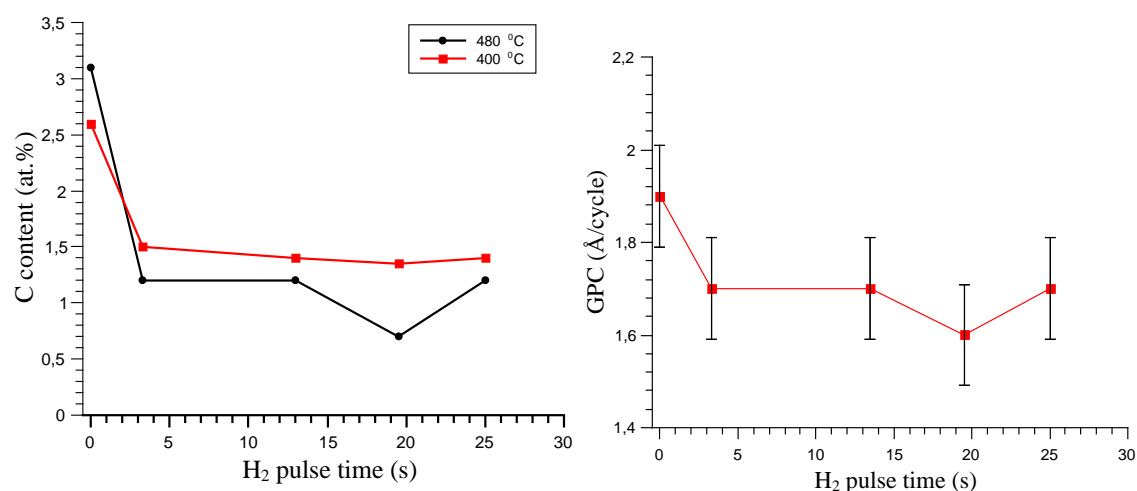


ABC-type pulsing for improved ALD of group 13 nitrides using trialkyl metal precursors

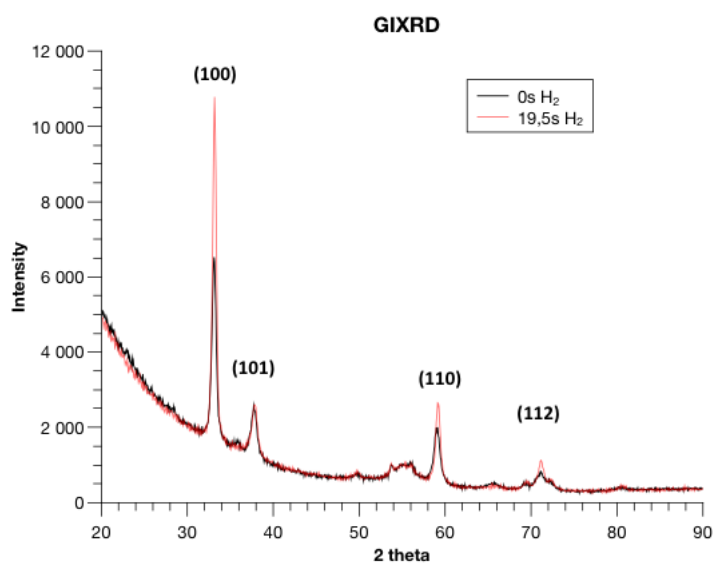
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XPS measurement of the films with different pulse length of H₂ showing decreasing C content upon increasing the H₂ pulse time. b) the GPC of the films with different H₂ pulse time deposited at 480 °C



GIXRD of the films deposited at 480 °C on Si (100) without (red line) and with a 19.5 s H₂ pulse (black line) showing crystalline hexagonal AlN were the crystallinity increases upon added H₂ pulse.